

Docket No.: 4425-154

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Han-Chao LAI ET AL.

U.S. Patent Application No. 09/888,494

Group Art Unit: 2814

Filed: June 26, 2001

Examiner: PHAM, LONG

For: METHOD FOR FORMING A METAL OXIDE SEMICONDUCTOR TYPE FIELD EFFECT TRANSISTOR

Dear Sir:

Transmitted herewith is a Response in the above identified application.

- ☒ No additional fee is required.
☐ Small entity status of this application has been established.
☐ Also attached:

The fee has been calculated as shown below:

	NO. OF CLAIMS	HIGHEST PREVIOUSLY PAID FOR	EXTRA CLAIMS	RATE	FEE
Total Claims	18	20	0	x \$ 18 =	\$ 0.00
Independent Claims	2	3	0	x \$ 84 =	\$ 0.00
If multiple claims newly presented, add \$280.00					
Fee for extension of time					
TOTAL FEE DUE					\$ 0.00

☐ A credit card authorization form in the amount of _____ is attached

☒ The Commissioner is hereby authorized to charge payment of any fees associated with this communication or credit any overpayment, to Deposit Account No. 07-1337, including any filing fees under 37 CFR 1.16 for presentation of extra claims and any patent application processing fees under 37 CFR 1.17.

Respectfully submitted,

LOWE HAUPTMAN GILMAN & BERNER, LLP

Benjamin J. Hauptman
Registration No.: 29,310

USPTO Customer No. 22429
1700 Diagonal Road, Suite 300
Alexandria, Virginia 22314
(703) 684-1111
(703) 518-5499 Facsimile
Date: October 1, 2003
BJH/jk